

CLAIM AMENDMENTS:

Please amend Claims 1, 8 and 9 as follows:

1. (Currently Amended) A photoelectric conversion device comprising:
 - a first-conductivity type first semiconductor region located in a pixel region;
 - a second-conductivity type second semiconductor region provided in the first semiconductor region and capable of accumulating photoelectric carriers in a floating state, wherein said first and second semiconductor regions form a photodiode;
 - a wiring for electrically connecting the second semiconductor region to a circuit element located outside the pixel region; and
 - a conductor provided on the wiring located inside the pixel region, via an insulator and capable of being kept at a stated potential, wherein said conductor is formed in the same layer as a light-screening layer in said pixel region.
2. (Original) The photoelectric conversion device according to claim 1, wherein the second semiconductor region is an island-shaped region surrounded by the first semiconductor region.
3. (Original) The photoelectric conversion device according to claim 1, wherein the second semiconductor region has a first part which is the island-shaped

region surrounded by the first semiconductor region and a second part surrounding the first part and having a lower impurity density than the first semiconductor region.

4. (Canceled).

5. (Original) The photoelectric conversion device according to claim 1, wherein the circuit element is an MOS transistor.

6. (Original) The photoelectric conversion device according to claim 1, wherein the circuit element comprises a resetting switch for resetting the potential of the second semiconductor region and an amplifying transistor for amplifying signals.

7. (Original) The photoelectric conversion device according to claim 1, wherein, to the circuit element, an accumulation circuit for accumulating a reset noise and a noise-reduction circuit for reducing the reset noise is connected.

8. (Currently Amended) The photoelectric conversion device according to claim 1, wherein the conductor ~~have~~ has a width smaller than the width of the wiring.

9. (Currently Amended) The photoelectric conversion device according to claim 1, wherein the conductor ~~have~~ has a width larger than the width of the wiring.

10. (Original) The photoelectric conversion device according to claim 1, which further comprises a terminal connected to a power source for keeping the conductor at a stated potential.

11. (Withdrawn) An image sensor comprising:
a light source;
an imaging device; and
the photoelectric conversion device according to claim 1.

12. (Withdrawn) The image sensor according to claim 11, wherein the photoelectric conversion device is provided in plurality in a one-dimensional fashion or staggered fashion on a mounting substrate.

13. (Withdrawn) The image sensor according to claim 11, which further comprises a wiring for supplying a reference voltage for keeping the conductor at a stated potential.

14. (Withdrawn) An image input system comprising:

an original-holding means for holding an original; the image sensor according to claim 11; and a control circuit for controlling the image sensor.

15. (Withdrawn) The image input system according to claim 14, wherein the original-holding means is an original stand having a transparent top surface, or an original-carrying holding-down member.

16. (Withdrawn) The image input system according to claim 14, which further comprises a reference voltage source that supplies a reference voltage for keeping the conductor at a stated potential.

17. (Previously Presented) The photoelectric conversion device according to Claim 1, wherein the conductor extends into a substantially square opening formed in a light-screening layer to define the pixel region, and along the wiring located inside the pixel region.